Silicon PNP Power Transistors 2SB1254

DESCRIPTION

- With TO-3PFa package
- Optimum for 60W HiFi output
- High foward current transfer ratio
- Low collector saturation voltage
- Complement to type 2SD1894

APPLICATIONS

- Power amplification

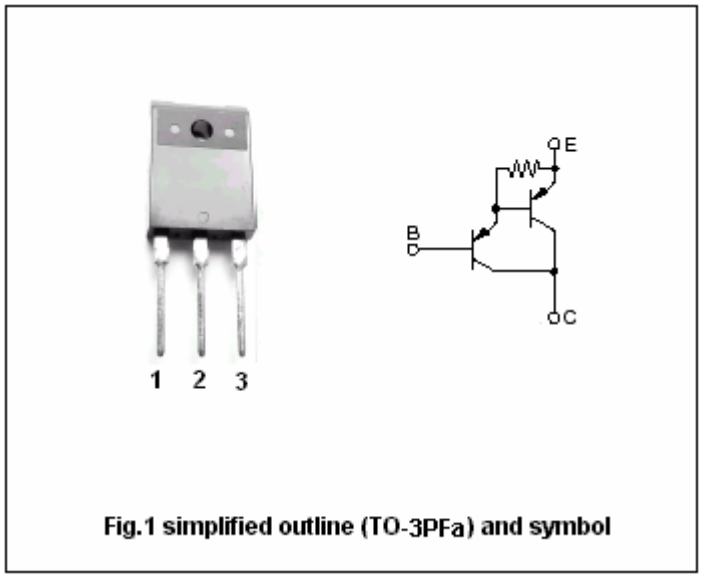

Fig.1 simplified outline (TO-3PFa) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-140	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-7	A
I_{CP}	Collector current-peak		-12	A
P_C	Collector power dissipation	T_C=25℃	70	W
		T_a=25℃	3	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter voltage	I_C=-30mA ; I_B=0	-140			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-6A ;I_B=-6mA			-2.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-6A ;I_B=-6mA			-3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-160V; I_E=0			-100	μA
I_{CEO}	Collector cut-off current	V_{CE}=-140V; I_B=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-100	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	2000			
h_{FE-2}	DC current gain	I_C=-6A ; V_{CE}=-5V	5000		30000	
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-10V;f=1MHz		20		MHz
Switching times						
t_{on}	Turn-on time	I_C=-6A; V_{CC}=50V I_{B1}=-I_{B2}=-6mA		1.0		μs
t_s	Storage time			1.5		μs
t_f	Fall time			1.2		μs

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PACKAGE OUTLINE

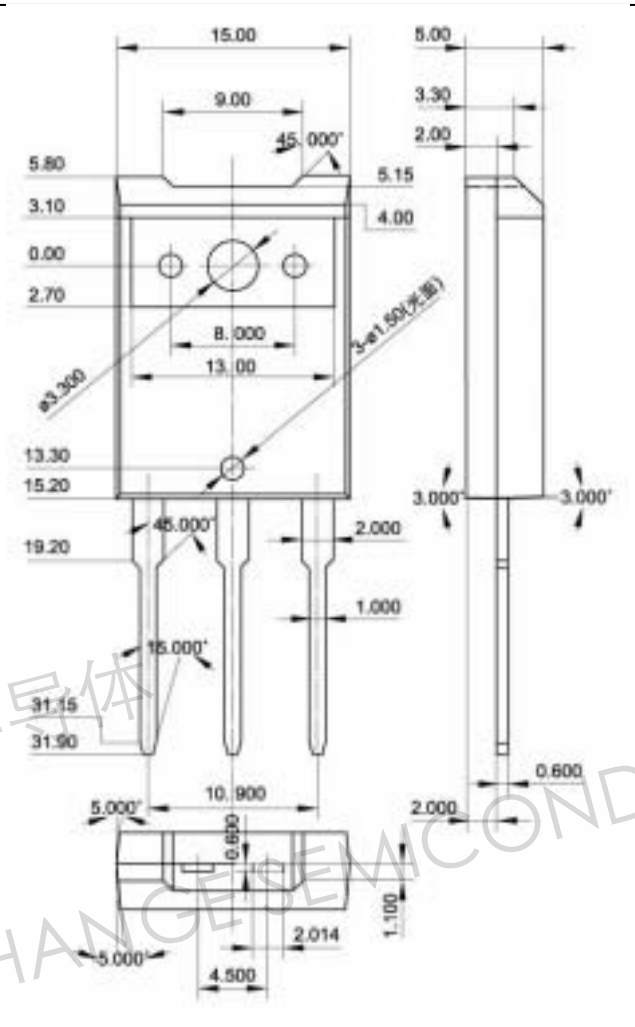

Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)